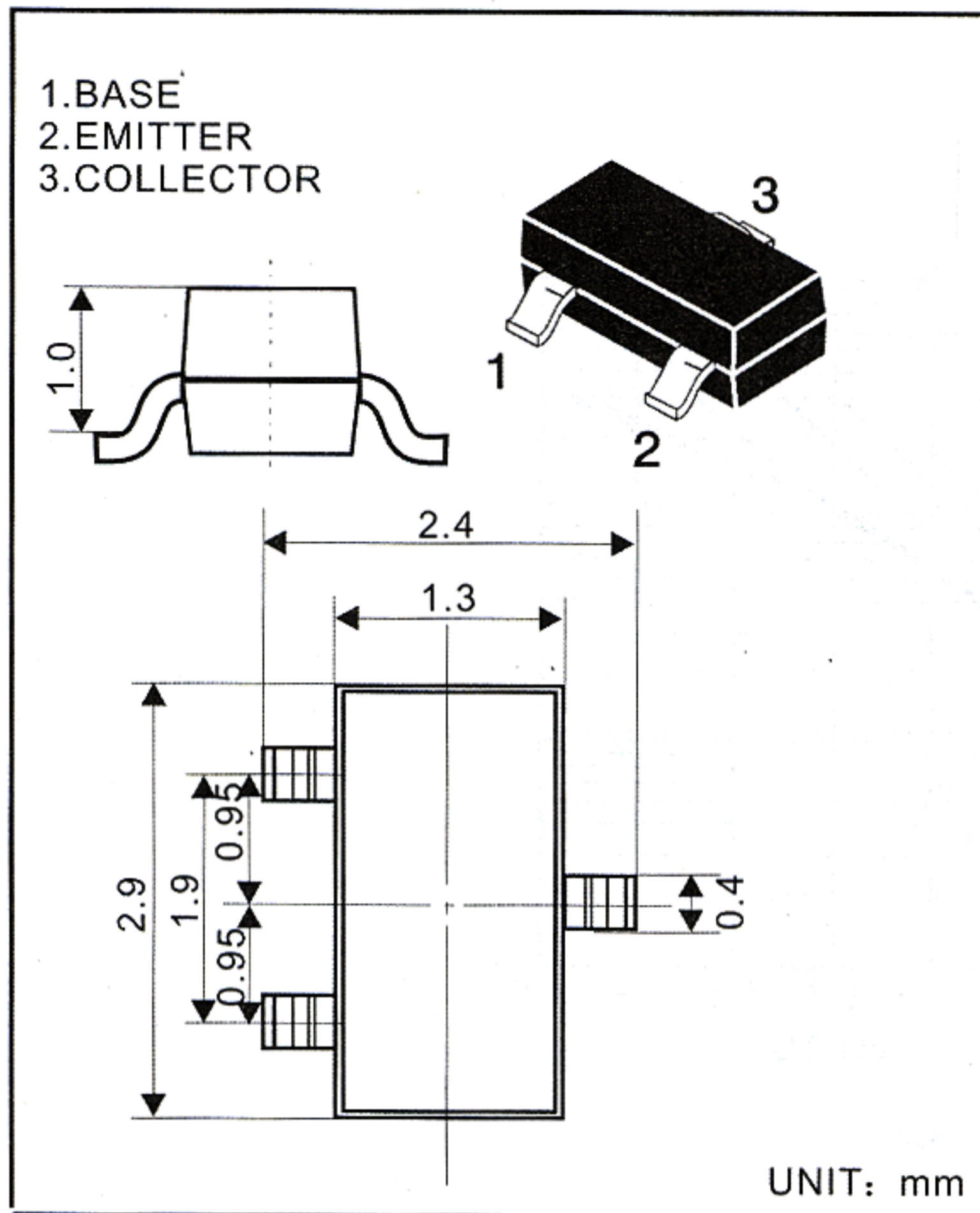


## BAS70 SERIES SCHOTTKY DIODE



### FEATURES

#### Power dissipation

$P_D$ : 200mW ( $T_{amb}=25^\circ C$ )

#### Forward current

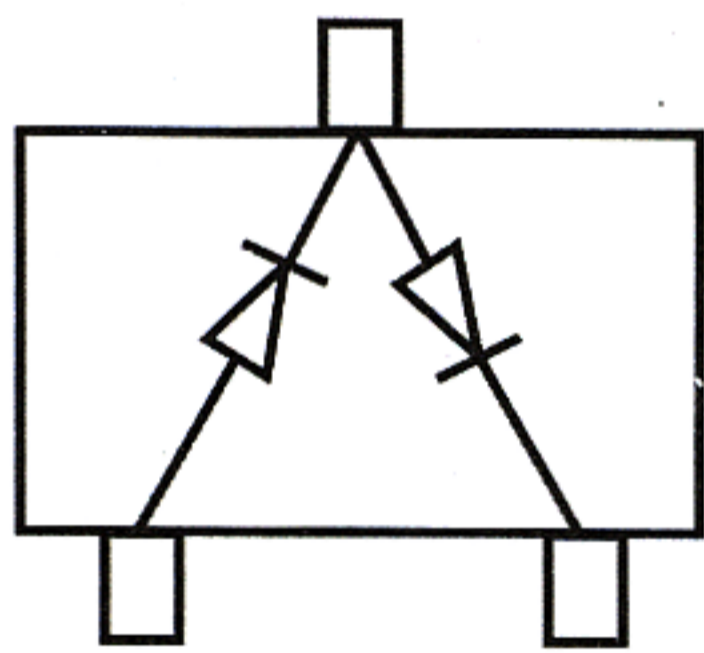
$I_F$ : 200mA

#### Reverse voltage

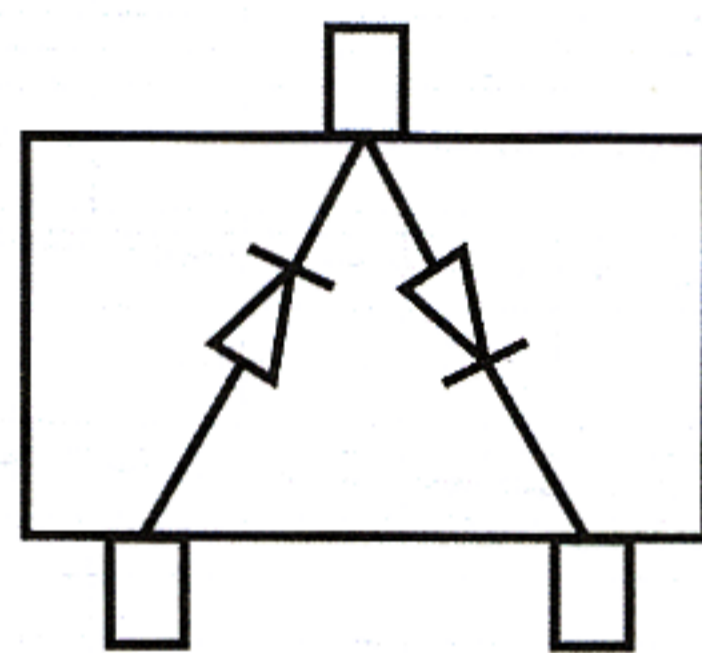
$V_R$ : 70V

#### Operating and storage junction temperature range

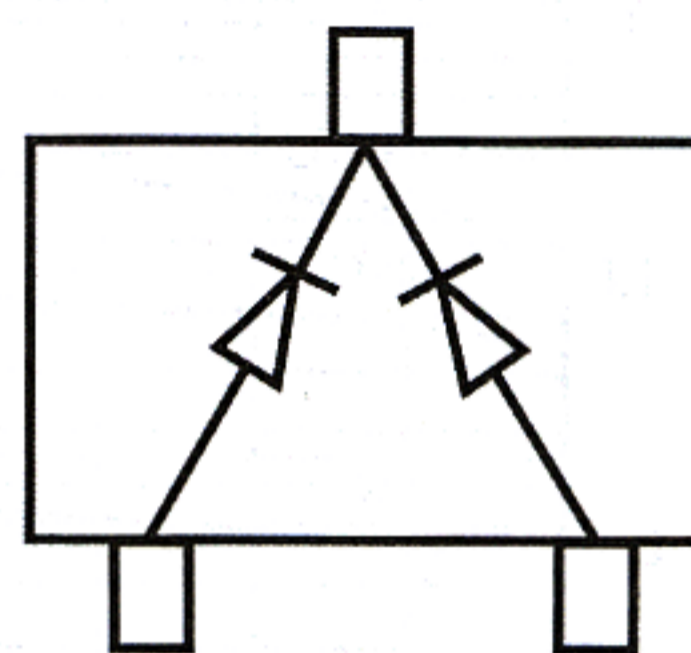
$T_J, T_{stg}$ :  $-55^\circ C$  to  $+150^\circ C$



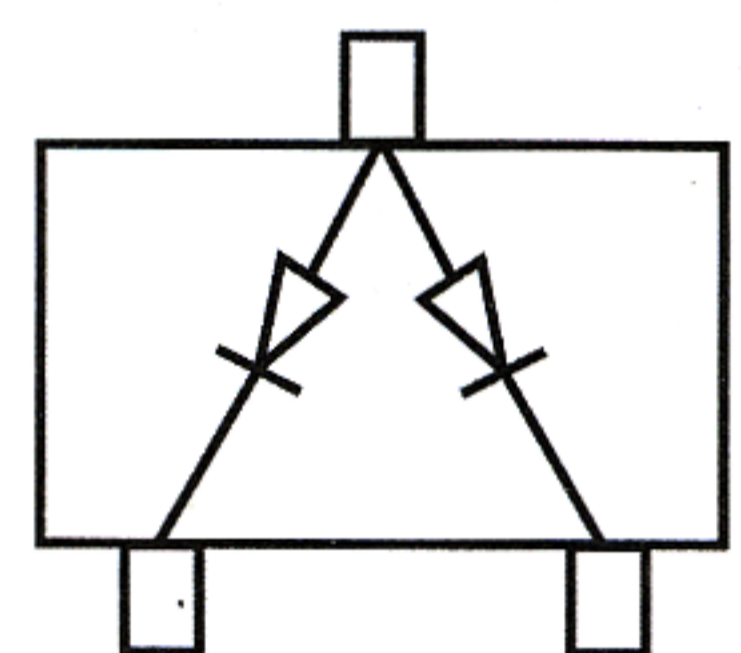
BAS70 MARKING: 73



BAS70-04 MARKING: 74



BAS70-05 MARKING: 75

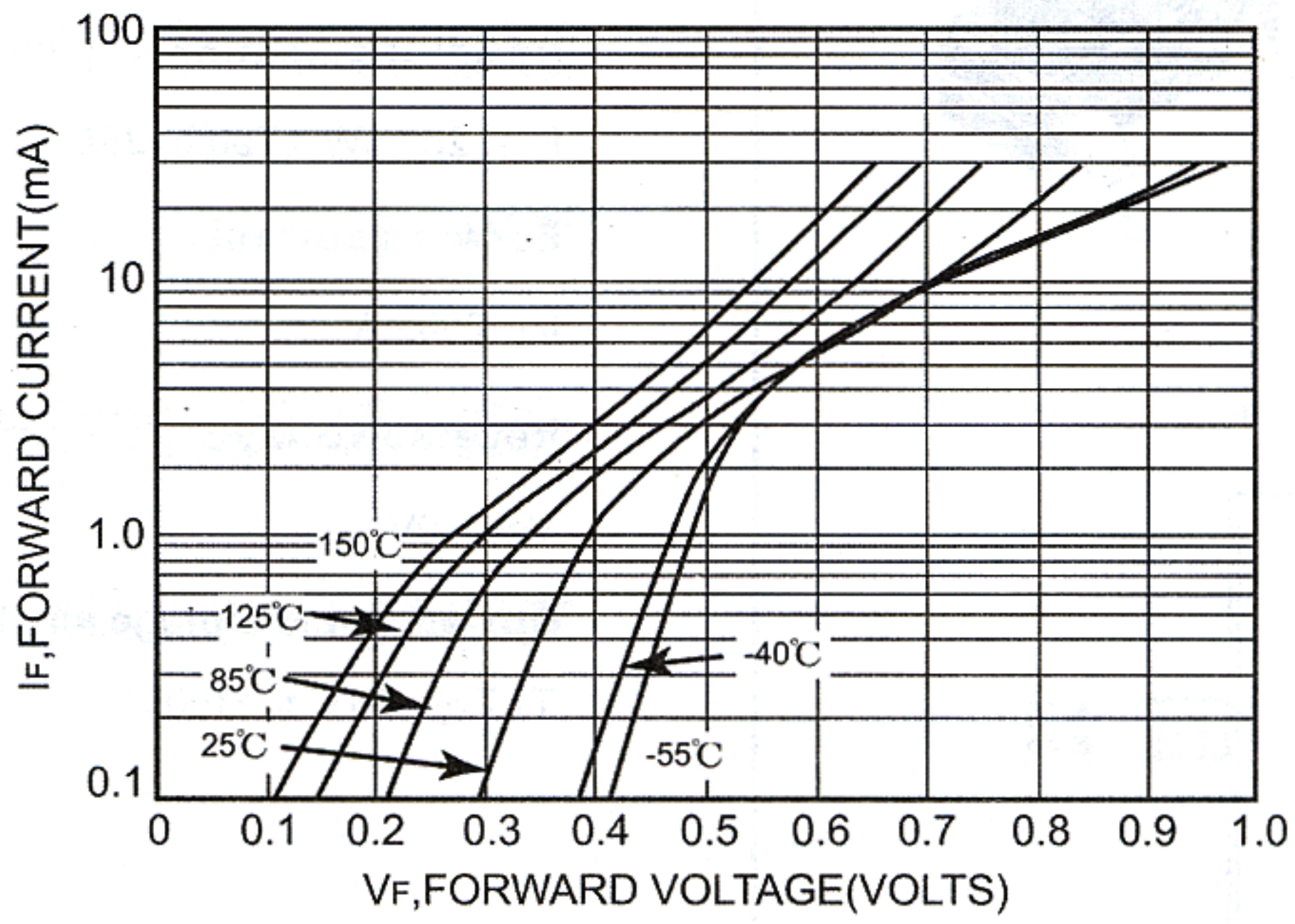


BAS70-06 MARKING: 76

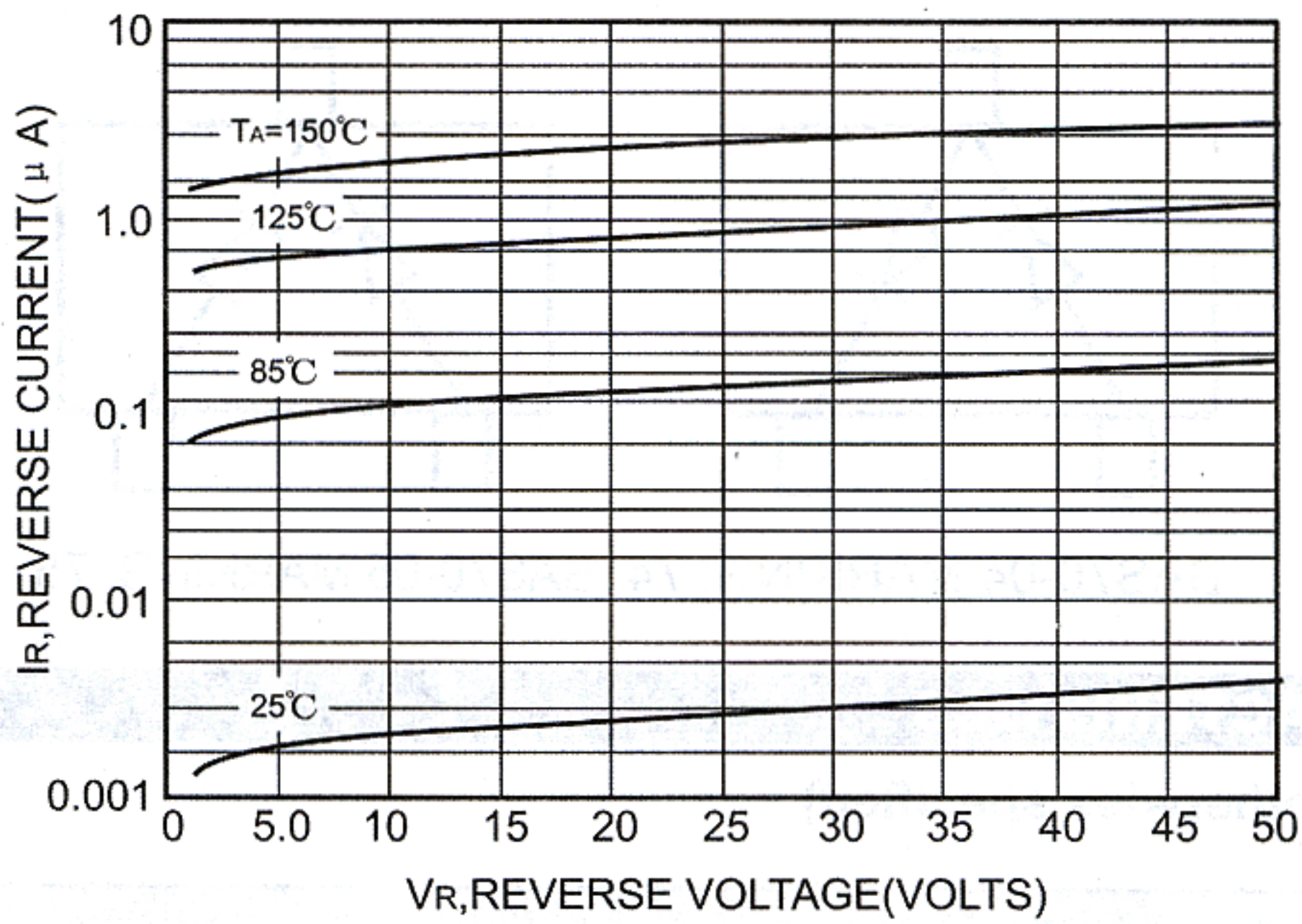
### ELECTRICAL CHARACTERISTICS

( $T_{amp}=25^\circ C$  unless otherwise specified)

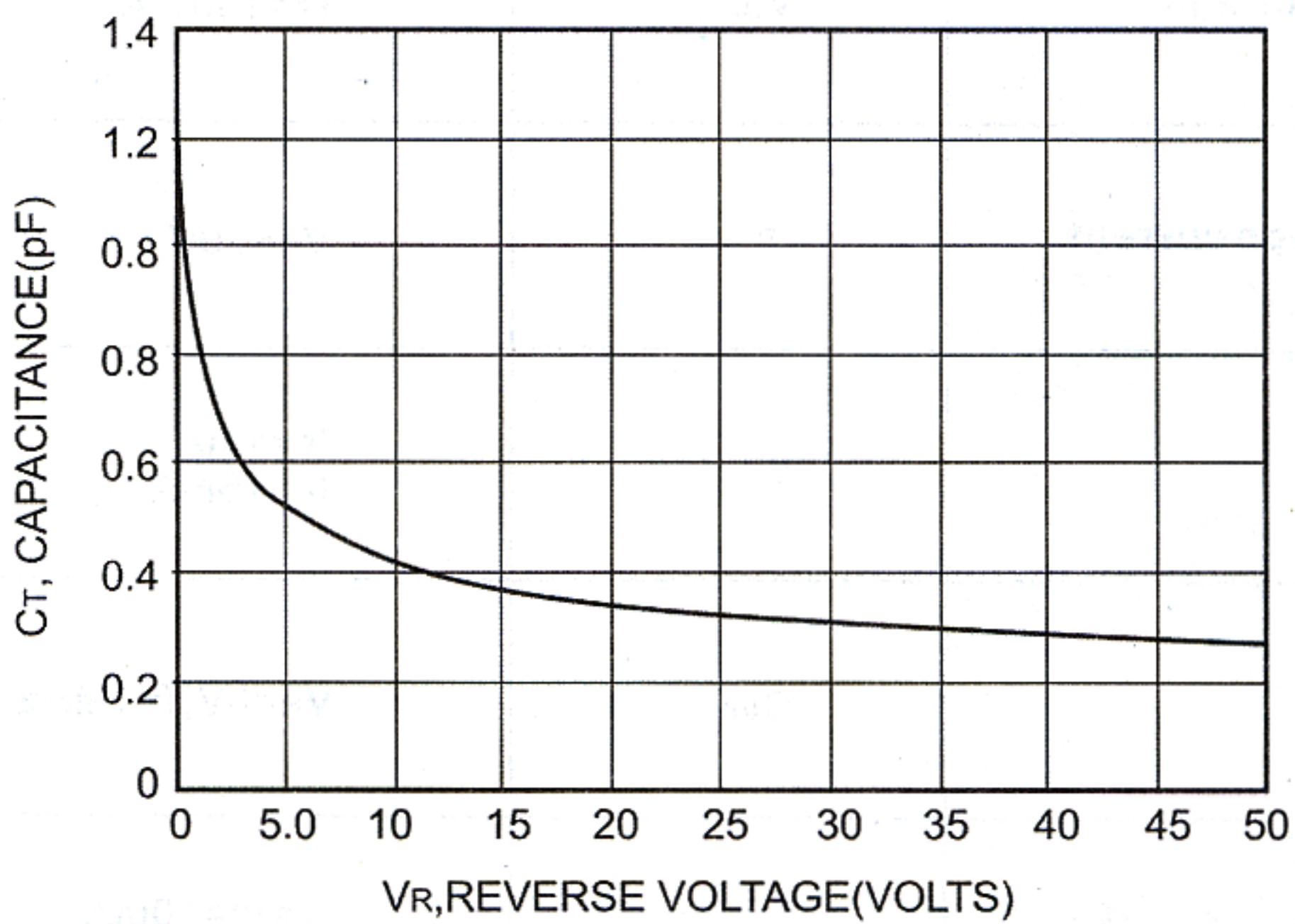
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	70		V
Reverse voltage leakage current	$I_R$	$V_R=50V$		100	nA
Forward voltage	$V_F$	$I_F=1mA$ $I_F=15mA$		410 1000	mV
Diode capacitance	$C_{tot}$	$V_R=0V, f=1MHz$		2	pF
Reverse recovery time	$t_{rr}$	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R$		5	ns



Forward Voltage



Reverse Current versus Reverse Voltage



Typical Capacitance